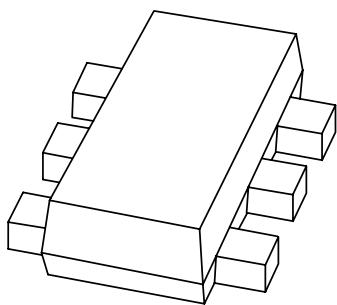


DATA SHEET



BC847BVN

NPN/PNP general purpose transistor

Product specification
Supersedes data of 2001 Aug 30

2001 Nov 07

NPN/PNP general purpose transistor**BC847BVN****FEATURES**

- 300 mW total power dissipation
- Very small 1.6 mm x 1.2 mm ultra thin package
- Excellent coplanarity due to straight leads
- Replaces two SC-75/SC-89 packaged transistors on same PCB area
- Reduced required PCB area
- Reduced pick and place costs.

APPLICATIONS

- General purpose switching and amplification
- Switch mode power supply complementary MOSFET driver
- Complementary driver for audio amplifiers.

DESCRIPTION

NPN/PNP transistor pair in a SOT666 plastic package.

MARKING

TYPE NUMBER	MARKING CODE
BC847BVN	13

PINNING

PIN	DESCRIPTION	
1, 4	emitter	TR1; TR2
2, 5	base	TR1; TR2
6, 3	collector	TR1; TR2

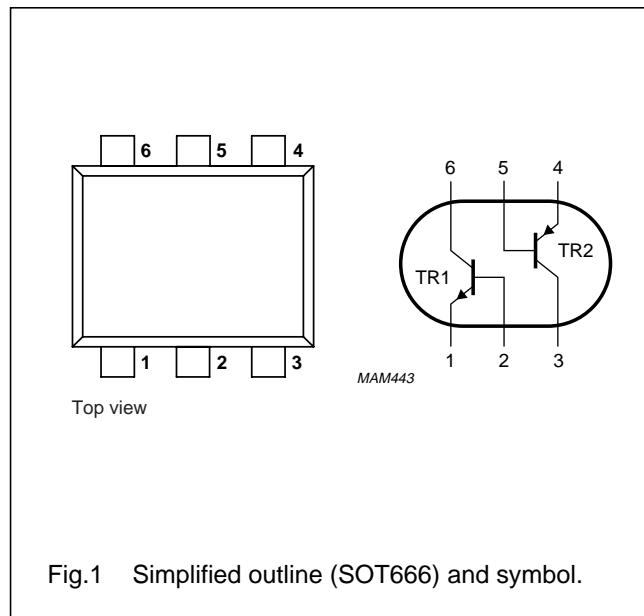


Fig.1 Simplified outline (SOT666) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per transistor; for the PNP transistor with negative polarity					
V_{CBO}	collector-base voltage	open emitter	—	50	V
V_{CEO}	collector-emitter voltage	open base	—	45	V
V_{EBO}	emitter-base voltage	open collector	—	5	V
I_C	collector current (DC)		—	100	mA
I_{CM}	peak collector current		—	200	mA
I_{BM}	peak base current		—	200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25^\circ\text{C}$; note 1	—	200	mW
T_{stg}	storage temperature		-65	+150	°C
T_j	junction temperature		—	150	°C
T_{amb}	operating ambient temperature		-65	+150	°C
Per device					
P_{tot}	total power dissipation	$T_{amb} \leq 25^\circ\text{C}$; note 1	—	300	mW

Note

1. Transistor mounted on an FR4 printed-circuit board.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	notes 1 and 2	416	K/W

Notes

1. Transistor mounted on an FR4 printed-circuit board.
2. The only recommended soldering is reflow soldering.

CHARACTERISTICS

 $T_{amb} = 25^\circ\text{C}$ unless otherwise specified.

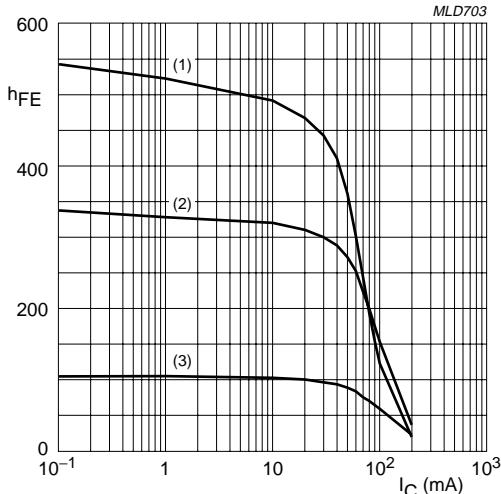
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Per transistor; for the PNP transistor with negative polarity						
I_{CBO}	collector-base cut-off current	$V_{CB} = 30\text{ V}; I_E = 0$	—	—	15	nA
		$V_{CB} = 30\text{ V}; I_E = 0; T_j = 150^\circ\text{C}$	—	—	5	μA
I_{EBO}	emitter-base cut-off current	$V_{EB} = 5\text{ V}; I_C = 0$	—	—	100	nA
h_{FE}	DC current gain	$V_{CE} = 5\text{ V}; I_C = 2\text{ mA}$	200	—	450	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	—	—	100	mV
		$I_C = 100\text{ mA}; I_B = 5\text{ mA}; \text{note 1}$	—	—	300	mV
V_{BEsat}	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	—	755	—	mV
f_T	transition frequency	$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}; f = 100\text{ MHz}$	100	—	—	MHz
NPN transistor						
V_{BE}	base-emitter turn-on voltage	$V_{CE} = 5\text{ V}; I_C = 2\text{ mA}$	580	655	700	mV
C_c	collector capacitance	$V_{CB} = 10\text{ V}; I_E = I_e = 0; f = 1\text{MHz}$	—	—	1.5	pF
C_e	emitter capacitance	$V_{EB} = 500\text{ mV}; I_C = I_c = 0; f = 1\text{MHz}$	—	11	—	pF
PNP transistor						
V_{BE}	base-emitter turn-on voltage	$V_{CE} = -5\text{ V}; I_C = -2\text{ mA}$	600	655	750	mV
C_c	collector capacitance	$V_{CB} = -10\text{ V}; I_C = I_c = 0; f = 1\text{MHz}$	—	—	2.2	pF
C_e	emitter capacitance	$V_{EB} = -500\text{ mV}; I_E = I_e = 0; f = 1\text{MHz}$	—	10	—	pF

Note

1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02$.

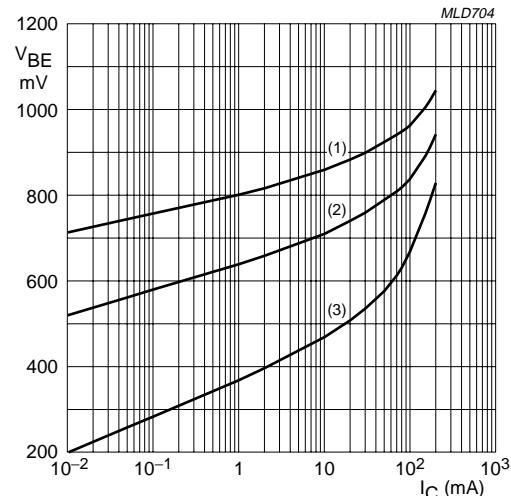
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TR1 (NPN); $V_{CE} = 5$ V.

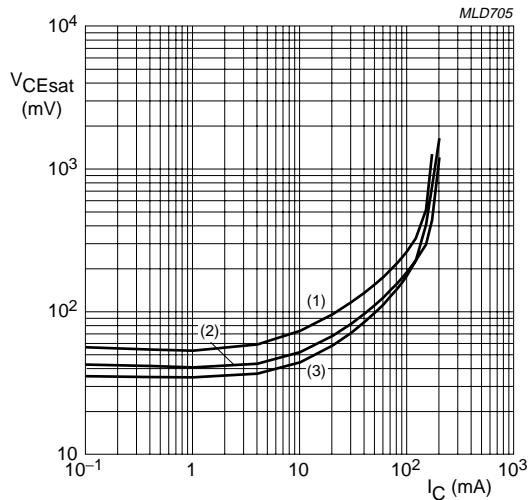
- (1) $T_{amb} = 150$ °C.
- (2) $T_{amb} = 25$ °C.
- (3) $T_{amb} = -55$ °C.

Fig.2 DC current gain as a function of collector current: typical values.

TR1 (NPN); $V_{CE} = 5$ V.

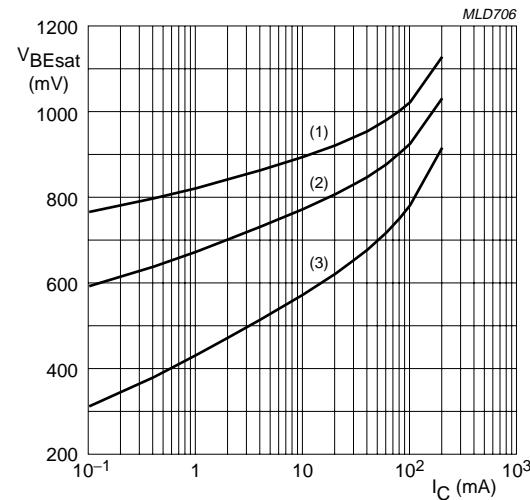
- (1) $T_{amb} = -55$ °C.
- (2) $T_{amb} = 25$ °C.
- (3) $T_{amb} = 150$ °C.

Fig.3 Base-emitter voltage as a function of collector current; typical values.

TR1 (NPN); $I_C/I_B = 20$.

- (1) $T_{amb} = 150$ °C.
- (2) $T_{amb} = 25$ °C.
- (3) $T_{amb} = -55$ °C.

Fig.4 Collector-emitter saturation voltage as a function of collector current: typical values.

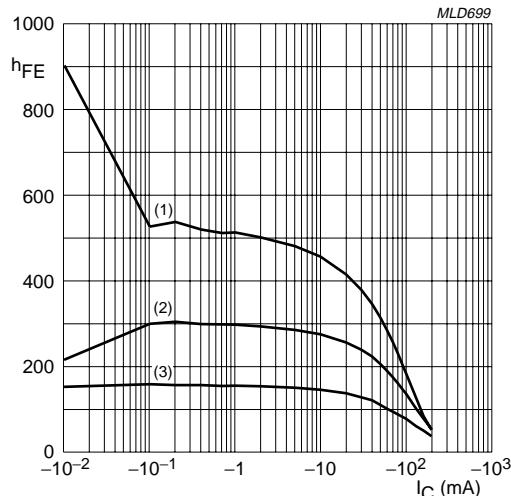
TR1 (NPN); $I_C/I_B = 20$.

- (1) $T_{amb} = -55$ °C.
- (2) $T_{amb} = 25$ °C.
- (3) $T_{amb} = 150$ °C.

Fig.5 Base-emitter saturation voltage as a function of collector current.

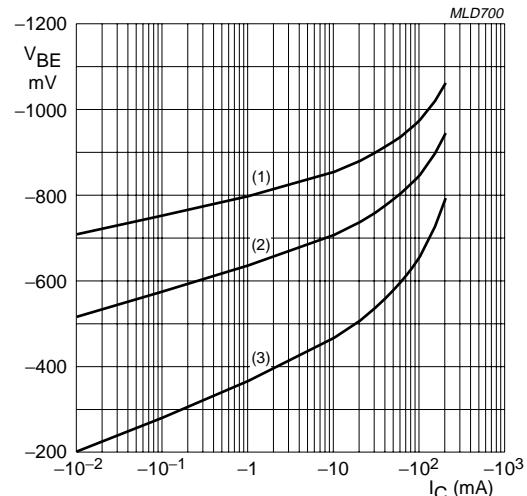
NPN/PNP general purpose transistor

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TR2 (PNP); $V_{CE} = -5$ V.

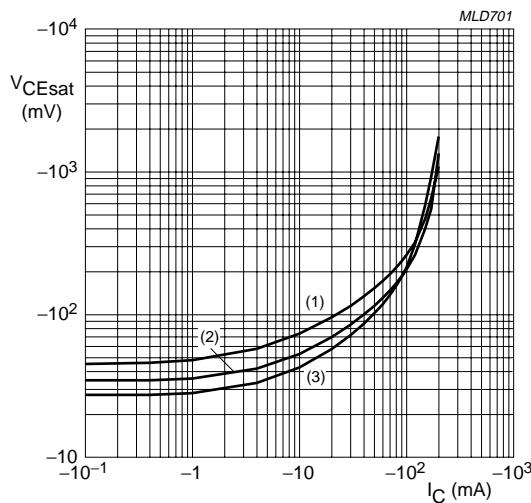
- (1) $T_{amb} = 150$ °C.
- (2) $T_{amb} = 25$ °C.
- (3) $T_{amb} = -55$ °C.

Fig.6 DC current gain as a function of collector current: typical values.

TR2 (PNP); $V_{CE} = -5$ V.

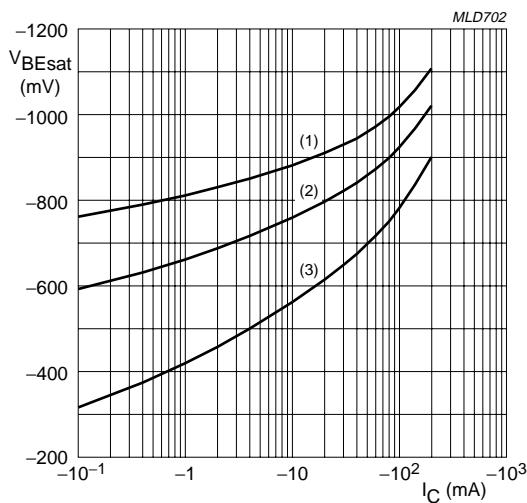
- (1) $T_{amb} = -55$ °C.
- (2) $T_{amb} = 25$ °C.
- (3) $T_{amb} = 150$ °C.

Fig.7 Base-emitter voltage as a function of collector current; typical values.

TR2 (PNP); $I_C/I_B = 20$.

- (1) $T_{amb} = 150$ °C.
- (2) $T_{amb} = 25$ °C.
- (3) $T_{amb} = -55$ °C.

Fig.8 Collector-emitter saturation voltage as a function of collector current: typical values.

TR2 (PNP); $I_C/I_B = 20$.

- (1) $T_{amb} = -55$ °C.
- (2) $T_{amb} = 25$ °C.
- (3) $T_{amb} = 150$ °C.

Fig.9 Base-emitter saturation voltage as a function of collector current.

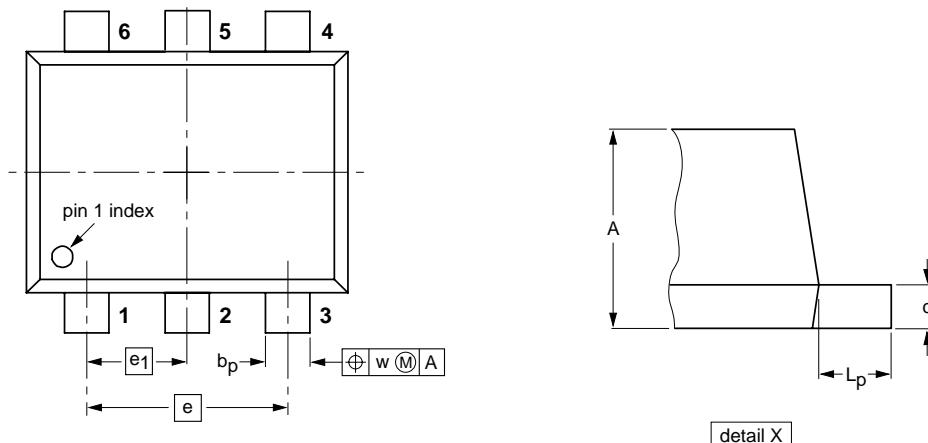
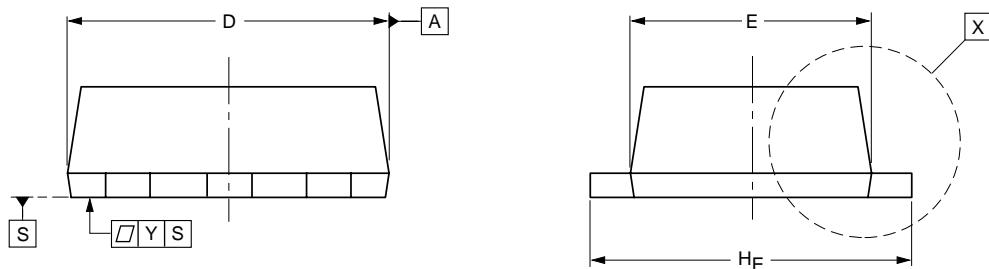
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PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT666



DIMENSIONS (mm are the original dimensions)

UNIT	A	b _p	c	D	E	e	e ₁	H _E	L _p	w	y
mm	0.6 0.5	0.27 0.17	0.18 0.08	1.7 1.5	1.3 1.1	1.0	0.5	1.7 1.5	0.3 0.1	0.1	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT666						-01-01-04 01-08-27

NPN/PNP general purpose transistor

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